

Part Description

The BTN6026 is a silicon BJT transistor available in bare die form and well suited for use in general purpose switching and amplifier applications. PNP Complement is BTP6990.

Key Parameters:

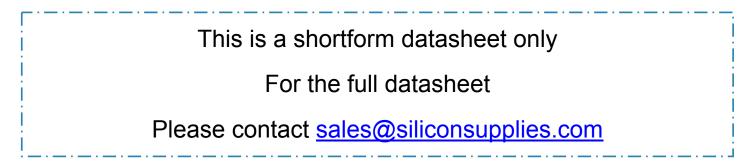
- · VCBO = 40V
- · VCEO = 20V
- · VEBO = 7V
- hFE = 400-1000 @ VCE = 2V, IC = 0.5A
- · VCE(Sat) = 0.15V @ IC = 1.6A, IB = 32mA
- fT = 200 MHz @ VCE = 2V, IE = 0A
- · COBO = 18pF @ VCB = 10V

Features

Very Low VCE(sat). Designed to provide performance equivalent to TOSHIBA 2SC5714 or ROHM 2SD2098

Die Size (Unsawn)

790µm X 790µm, 31 Mils X 31 Mils



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